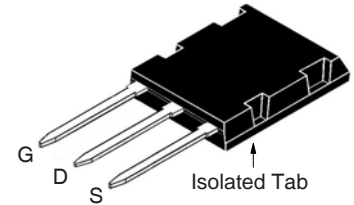


**Polar3™ HiPerFET™
Power MOSFET**
IXFL210N30P3
(Electrically Isolated Tab)

 N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Rectifier


$$\begin{aligned}
 V_{DSS} &= 300V \\
 I_{D25} &= 108A \\
 R_{DS(on)} &\leq 16m\Omega \\
 t_{rr} &\leq 250ns
 \end{aligned}$$

ISOPLUS264


 G = Gate D = Drain
 S = Source

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 300 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$ | 300 | V |
| V_{GSS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 108 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM} | 550 | A |
| I_A | $T_C = 25^\circ\text{C}$ | 105 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 4 | J |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$ | 35 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 520 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ\text{C}$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ\text{C}$ |
| F_C | Mounting Force | 40..120 / 9..27 | N/lb |
| V_{ISOL} | 50/60 Hz, RMS $t = 1$ min | 2500 | V~ |
| | $I_{ISOL} \leq 1$ mA $t = 1$ s | 3000 | V~ |
| Weight | | 8 | g |

Features

- Silicon Chip on Direct-Copper-Bond Substrate
 - High Power Dissipation
 - Isolated Mounting Surface
 - 2500V~ Electrical Isolation
- Dynamic dv/dt Rating
- Avalanche Rated
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$
- Low Drain-to-Tab Capacitance
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|----------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 3mA$ | 300 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8mA$ | 2.5 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 20V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ Note 2, $T_J = 125^\circ\text{C}$ | | | 50 μA 1.5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 105A$, Note 1 | | | 16 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|--|--|------|------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}, I_D = 60\text{A}$, Note 1 | 60 | 100 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 16.2 | nF |
| C_{oss} | | | 2550 | pF |
| C_{rss} | | | 42 | pF |
| R_{Gi} | Gate Input Resistance | | 1.0 | Ω |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{DSS}$ $R_G = 1\Omega$ (External) | | 46 | ns |
| t_r | | | 25 | ns |
| $t_{d(off)}$ | | | 94 | ns |
| t_f | | | 13 | ns |
| $Q_{g(on)}$ | | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{DSS}$ | | 268 |
| Q_{gs} | | | 80 | nC |
| Q_{gd} | | | 72 | nC |
| R_{thJC} | | | | 0.24°C/W |
| R_{thCS} | | 0.15 | | $^\circ\text{C/W}$ |

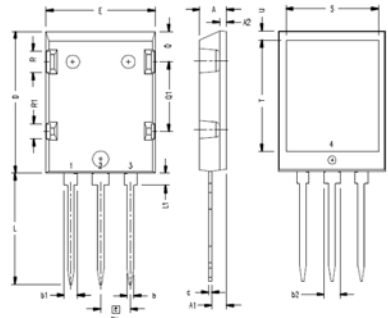
Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|----------|--|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_s | $V_{GS} = 0\text{V}$ | | | 210 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 840 A |
| V_{SD} | $I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 105\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$ | | | 250 ns |
| Q_{RM} | | | 4.1 | μC |
| I_{RM} | | | 28 | A |

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Part must be heatsunk for high-temp I_{DSS} measurement.

ISOPLUS264 (IXFL) OUTLINE



1 = Gate
2,4 = Drain
3 = Source

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .190 | .205 | 4.83 | 5.21 |
| A1 | .102 | .118 | 2.59 | 3.00 |
| A2 | .046 | .055 | 1.17 | 1.40 |
| b | .045 | .055 | 1.14 | 1.40 |
| b1 | .087 | .102 | 2.21 | 2.59 |
| b2 | .111 | .126 | 2.82 | 3.20 |
| c | .020 | .029 | 0.51 | 0.74 |
| D | 1.020 | 1.040 | 25.91 | 26.42 |
| E | .770 | .799 | 19.56 | 20.29 |
| e | .215 BSC | | 5.46 BSC | |
| L | .780 | .820 | 19.81 | 20.83 |
| L1 | .080 | .102 | 2.03 | 2.59 |
| Q | .210 | .235 | 5.33 | 5.97 |
| Q1 | .490 | .513 | 12.45 | 13.03 |
| R | .150 | .180 | 3.81 | 4.57 |
| R1 | .100 | .130 | 2.54 | 3.30 |
| S | .668 | .690 | 16.97 | 17.53 |
| T | .801 | .821 | 20.34 | 20.85 |
| U | .065 | .080 | 1.65 | 2.03 |

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

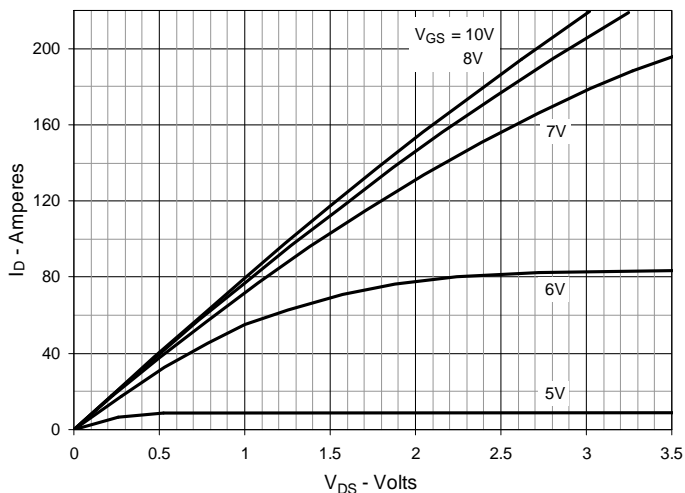
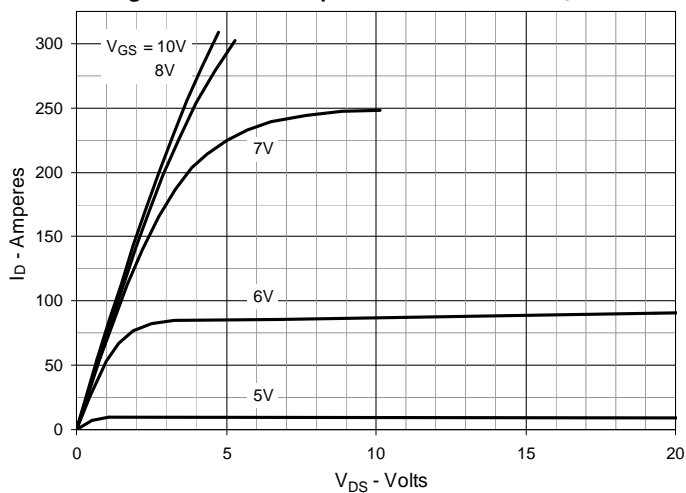
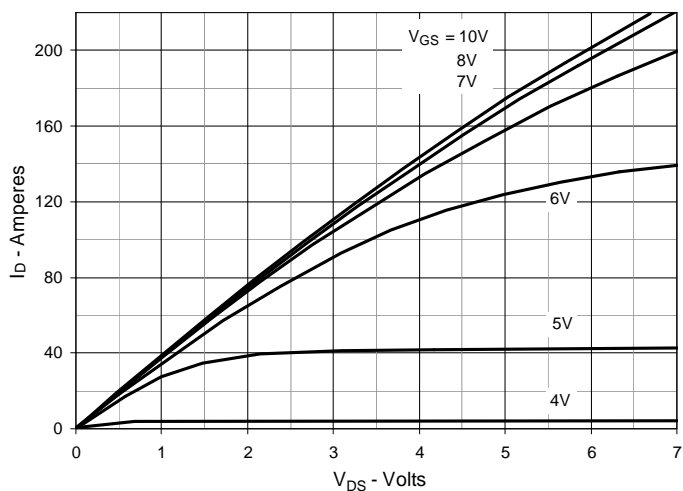
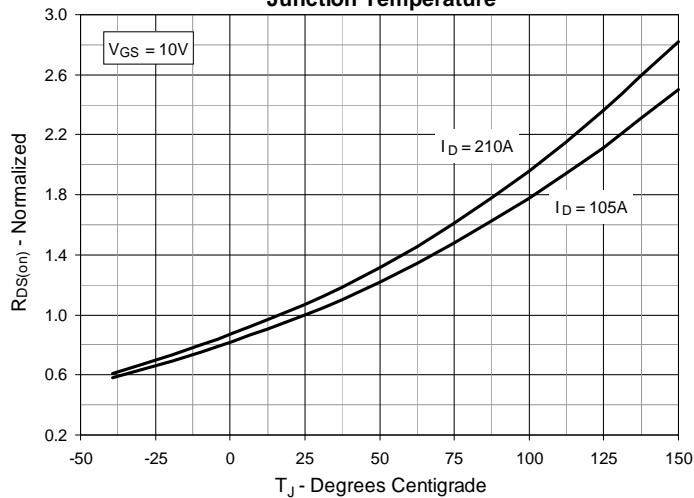
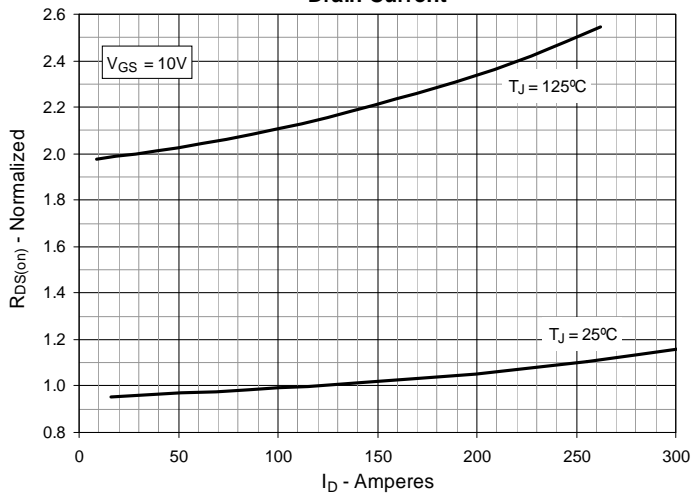
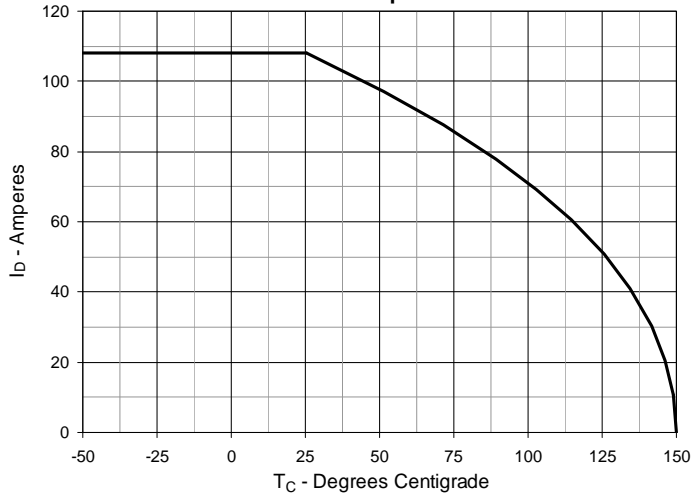
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 105\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 105\text{A}$ Value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature


Fig. 7. Input Admittance

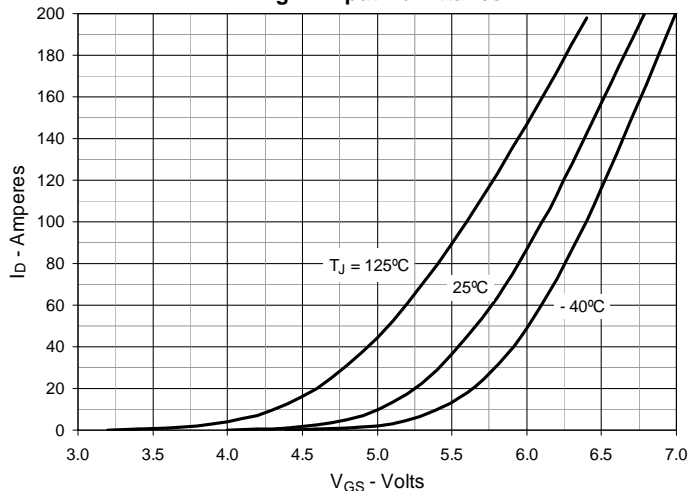


Fig. 8. Transconductance

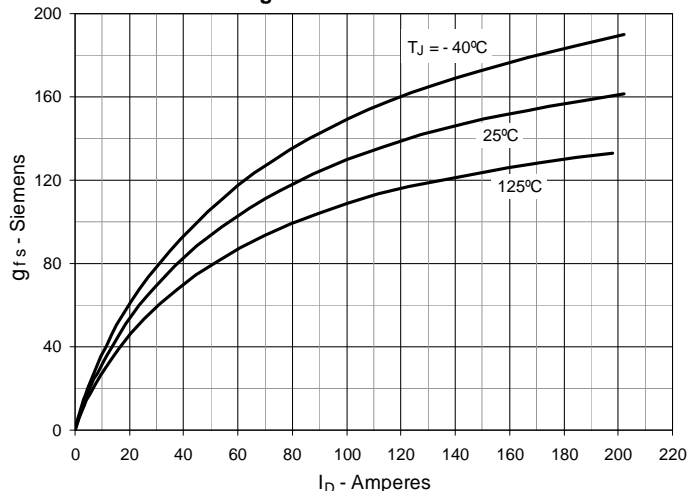


Fig. 9. Forward Voltage Drop of Intrinsic Diode

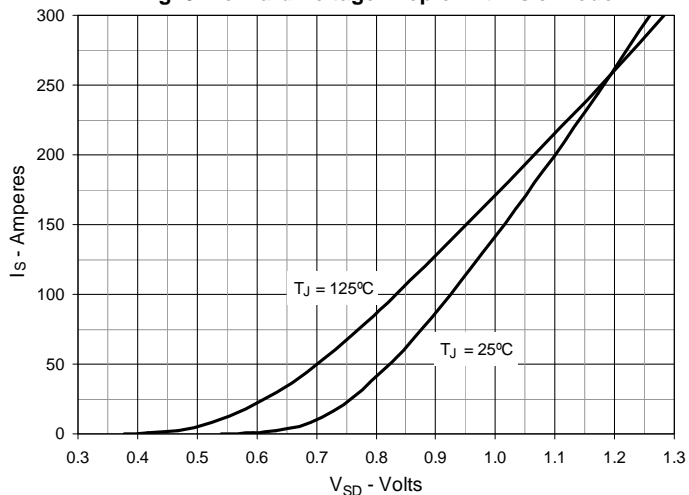


Fig. 10. Gate Charge

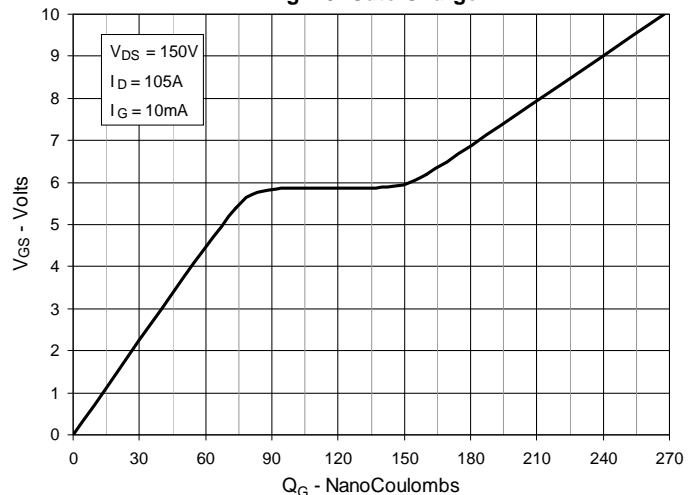


Fig. 11. Capacitance

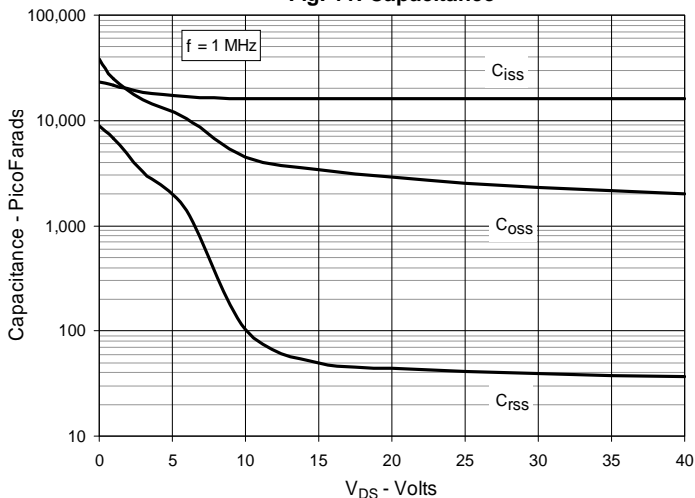


Fig. 12. Forward-Bias Safe Operating Area

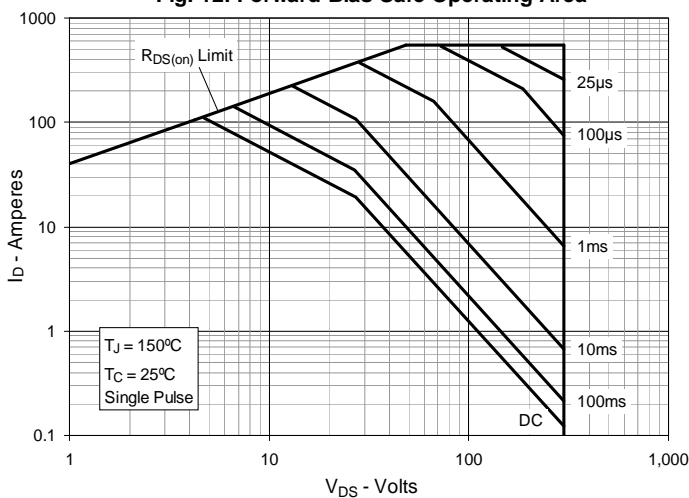
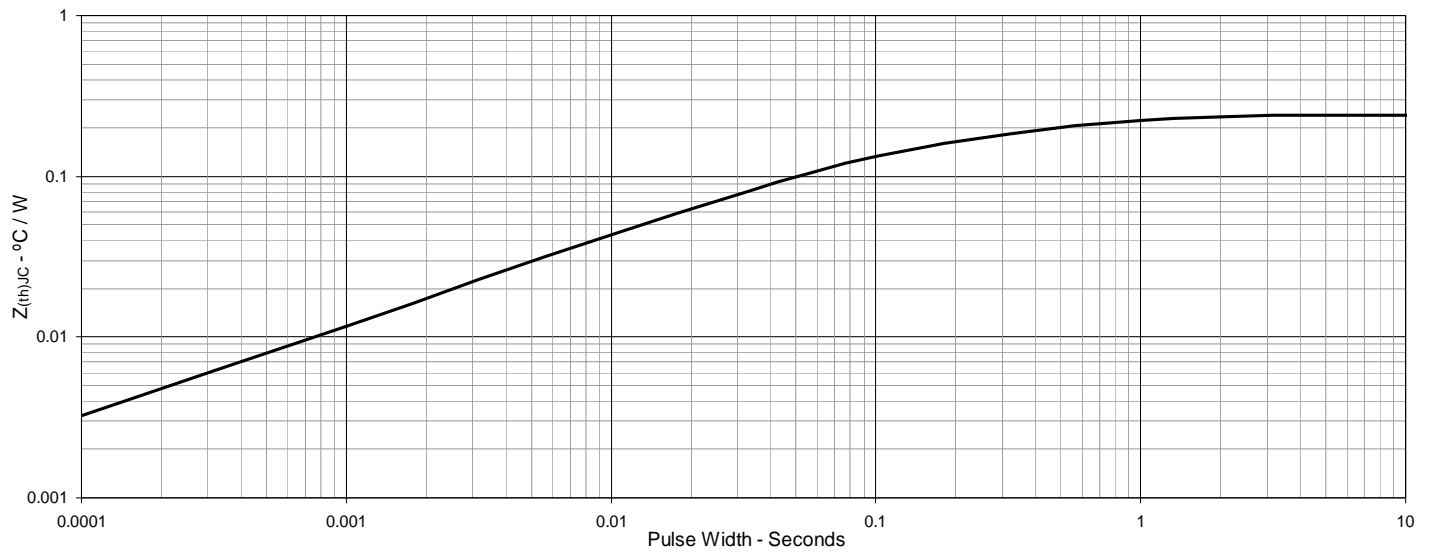


Fig. 13. Maximum Transient Thermal Impedance





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